

JTDA 150A

145 Watts, 36 Volts, Pulsed Avionics 960 - 1215 MHz

GENERAL DESCRIPTION

The JTDA-150A is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 960-1215 MHz. The transistor includes input and output prematch for broadband performance. The device has gold thin-film metallization and diffused ballasting for proven highest MTTF. Low thermal resistance Solder Sealed Package reduces junction temperature, extends life.

ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C² 350 Watts

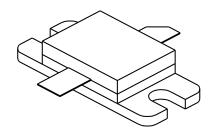
Maximum Voltage and Current

BVcesCollector to Base Voltage50 VoltsBVeboEmitter to Base Voltage3.5 VoltsIcCollector Current15 Amps

Maximum Temperatures

Storage Temperature $- 65 \text{ to} + 200 ^{\circ}\text{C}$ Operating Junction Temperature $+ 200 ^{\circ}\text{C}$

CASE OUTLINE 55KT, STYLE 1



ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout Pin Pg η _c VSWR	Power Out Power Input Power Gain Collector Efficiency Load Mismatch Tolerance	F = 960-1215 MHz Vcc = 36 Volts PW = Note 1 DF = Note 1 F = 1215 MHz	145 8	45	24 3:1	Watts Watts dB %

BVebo BVces h _{FE}	Emitter to Base Breakdown Collector to Emitter Breakdown DC - Current Gain	Ie = 20 mA Ic = 60 mA Ic = 5.0A, Vce = 5 V	3.5 55 20		Volts Volts
$\theta \mathbf{j} \mathbf{c}^2$	Thermal Resistance	,		0.5	°C/W

Note 1: JTIDS Pulse = 7 Micorseconds On / Off for 3.3 Millisec, 22 % Long term duty

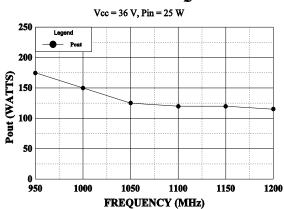
2: At rated pulse conditions

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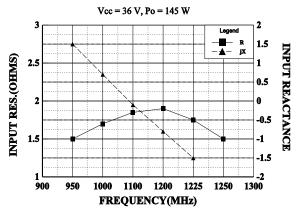
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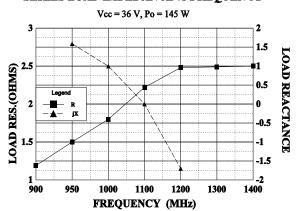
POWER OUTPUT vs FREQUENCY



SERIES INPUT IMPEDANCE vs FREQUENCY

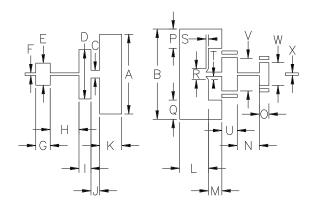


SERIES LOAD IMPEDANCE vs FREQUENCY



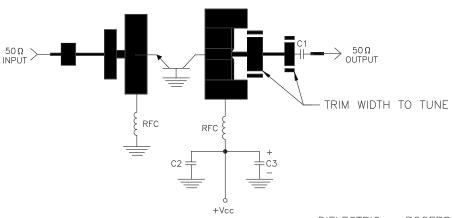


	REVISIONS					
ZONE	REV	DESCRIPTION	DATE	APPROVED		



DIM	INCHES		
А	.830		
В	.940		
С	.080		
D	.515		
Е	.230		
F	.026		
G	.150		
Н	.300		
- 1	.125		
J	.090		
K	.230		
L	.300		
М	.140		
N	.230		
0	.100		
Р	.200		
Q	.200		
R	.115		
S	.025		
Т	.035		
U	.160		
V	.350		
W	.240		
Χ	.026		

JTDA 150A TEST CIRCUIT



DIELECTRIC = ROGERS 6010 Er = 10.2, t = 25 C1, C2 = 82pF CHIP ATC "A" C3 = 1000 MFD @ 50V RFC = 5 turns #22 wire 1/16" I.D.



cage 0PJR2	DWG NO.	JTDA	150	0A	REV	A
	SCALE	1/1	SI	HEET		